SLIS009A – APRIL 1992 – REVISED SEPTEMBER 1995

- Low r<sub>DS(on)</sub> . . . 1.3 Ω Typical
- Avalanche Energy . . . 75 mJ
- Eight Power DMOS Transistor Outputs of 250-mA Continuous Current
- 1.5-A Pulsed Current Per Output
- Output Clamp Voltage at 45 V
- Four Distinct Function Modes
- Low Power Consumption

#### description

This power logic 8-bit addressable latch controls open-drain DMOS transistor outputs and is designed for general-purpose storage applications in digital systems. Specific uses include working registers, serial-holding registers, and decoders or demultiplexers. This is a multifunctional device capable of storing single-line data in eight addressable latches with 3-to-8 decoding or demultiplexing mode active-low DMOS outputs.

Four distinct modes of operation are selectable by controlling the clear ( $\overline{CLR}$ ) and enable ( $\overline{G}$ ) inputs as enumerated in the function table. In the addressable-latch mode, data at the data-in (D) terminal is written into the addressed latch. The addressed DMOS transistor output inverts the data input with all unaddressed DMOS-transistor outputs remaining in their previous states. In the memory mode, all DMOS-transistor outputs remain in their previous states and are unaffected by the data or address inputs. To eliminate the possibility of entering erroneous data in the latch, enable  $\overline{G}$  should be held high (inactive) while the address lines are changing. In the 3-to-8 decoding

(TOP VIEW)									
PGND	1	υ	20	] PGND					
V <sub>CC</sub> [	2		19	] CLR					
S0 [	3		18	] D					
DRAIN0	4		17	DRAIN7					
DRAIN1	5		16	DRAIN6					
DRAIN2	6		15	DRAIN5					
DRAIN3	7		14	DRAIN4					
S1 [	8		13	] <u>G</u>					
LGND	9		12	] S2					
PGND	10		11	] PGND					

FUNCTION TABLE

INF	PUT	s	OUTPUT OF	EACH	
CLR	G	D	ADDRESSED DRAIN	OTHER DRAIN	FUNCTION
H H	L L	H L	L H	Q <sub>io</sub> Q <sub>io</sub>	Addressable Latch
н	Н	Х	Q <sub>io</sub>	Q <sub>i0</sub>	Memory
L	L L	H L	L H	H H	8-Line Demultiplexer
L	Н	Х	н	Н	Clear

#### LATCH SELECTION TABLE

SELE	CT IN	DRAIN	
S2	S1	S0	ADDRESSED
L	L	L	0
L	L	н	1
L	Н	L	2
L	Н	н	3
н	L	L	4
н	L	Н	5
Н	Н	L	6
Н	Н	Н	7

or demultiplexing mode, the addressed output is inverted with respect to the D input and all other outputs are high. In the clear mode, all outputs are high and unaffected by the address and data inputs.

Separate power and logic level ground pins are provided to facilitate maximum system flexibility. Pins 1, 10, 11, and 20 are internally connected, and each pin must be externally connected to the power system ground in order to minimize parasitic inductance. A single-point connection between pin 9, logic ground (LGND), and pins 1, 10, 11, and 20, power ground (PGND) must be externally made in a manner that reduces crosstalk between the logic and load circuits.

The TPIC6259 is characterized for operation over the operating case temperature range of  $-40^{\circ}$ C to  $125^{\circ}$ C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



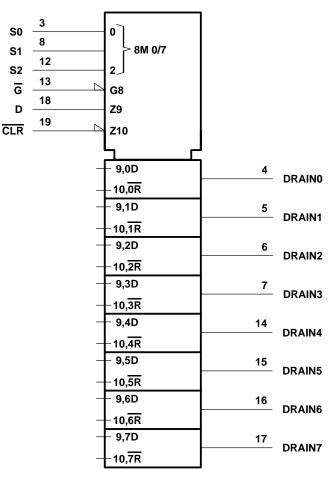
Copyright © 1995, Texas Instruments Incorporated

POST OFFICE BOX 655303 

DALLAS, TEXAS 75265
POST OFFICE BOX 1443 
HOUSTON, TEXAS 77251–1443

SLIS009A - APRIL 1992 - REVISED SEPTEMBER 1995

### logic symbol<sup>†</sup>

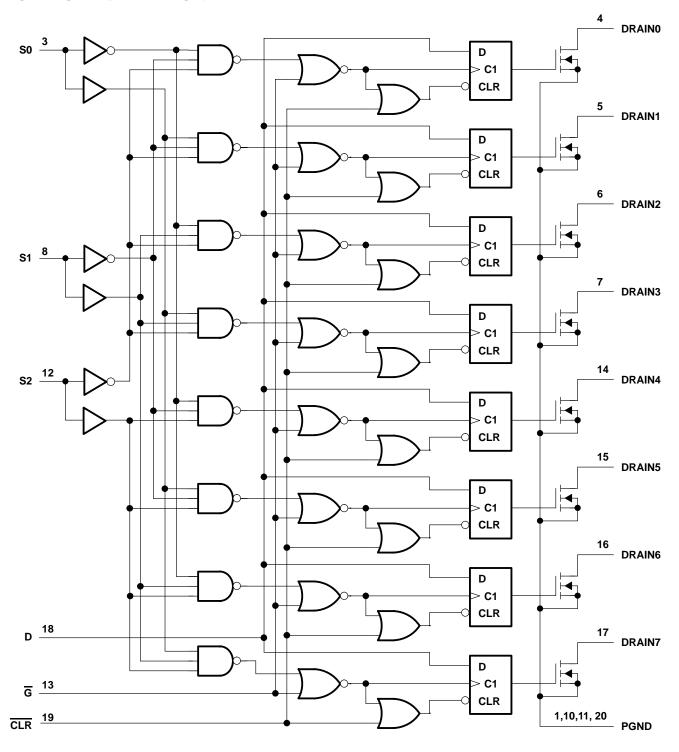


<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



SLIS009A - APRIL 1992 - REVISED SEPTEMBER 1995

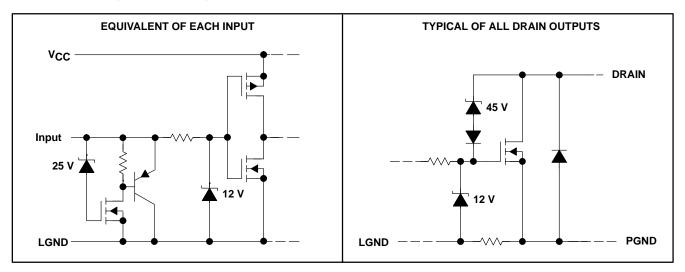
logic diagram (positive logic)





SLIS009A - APRIL 1992 - REVISED SEPTEMBER 1995

#### schematic of inputs and outputs



# absolute maximum ratings over the recommended operating case temperature range (unless otherwise noted) $\!\!\!\!^\dagger$

Logic supply voltage, V <sub>CC</sub> (see Note 1)	
Logic input voltage range, V <sub>I</sub>	–0.3 V to 7 V
Power DMOS drain-to-source voltage, V <sub>DS</sub> (see Note 2)	
Continuous source-drain diode anode current	1 A
Pulsed source-drain diode anode current	2 A
Pulsed drain current, each output, all outputs on, I <sub>Dn</sub> , T <sub>A</sub> = 25°C (see Note 3)	750 mA
Continuous drain current, each output, all outputs on, I <sub>Dn</sub> , T <sub>A</sub> = 25°C	250 mA
Peak drain current single output, I <sub>DM.</sub> T <sub>A</sub> = 25°C (see Note 3)	2 A
Single-pulse avalanche energy, E <sub>AS</sub> (see Note 4)	75 mJ
Avalanche current, I <sub>AS</sub> (see Note 4)	1 A
Continuous total power dissipation	See Dissipation Rating Table
Operating virtual junction temperature range, T <sub>J</sub>	−40°C to 150°C
Storage temperature range, T <sub>stg</sub>	–65°C to 150°C
Lead temperature 1.6 mm (1/16 inch) from case for 10 seconds	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values are with respect to LGND and PGND.

- 2. Each power DMOS source is internally connected to PGND.
- 3. Pulse duration  $\leq 100 \ \mu$ s, duty cycle  $\leq 2\%$
- 4. DRAIN supply voltage = 15 V, starting junction temperature, (TJS) = 25°C, L = 100 mH, IAS = 1 A (see Figure 4).

#### DISSIPATION RATING TABLE

PACKAGE	T <sub>A</sub> ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 125°C POWER RATING
DW	1125 mW	9.0 mW/°C	225 mW
Ν	1150 mW	9.2 mW/°C	230 mW



SLIS009A - APRIL 1992 - REVISED SEPTEMBER 1995

# recommended operating conditions over recommended operating temperature range (unless otherwise noted)

	MIN	MAX	UNIT
Logic supply voltage, V <sub>CC</sub>	4.5	5.5	V
High-level input voltage, VIH	0.85 V <sub>CC</sub>		V
Low-level input voltage, VIL		0.15 V <sub>CC</sub>	V
Pulsed drain output current, $T_C = 25^{\circ}C$ , $V_{CC} = 5 V$ (see Notes 3 and 5)	-1.8	1.5	А
Setup time, D high before $\overline{G}$ , t <sub>SU</sub> (see Figure 2)	10		ns
Hold time, D high after $\overline{G}$ , t <sub>h</sub> (see Figure 2)	5		ns
Pulse duration, t <sub>w</sub> (see Figure 2)	15		ns
Operating case temperature, T <sub>C</sub>	-40	125	°C

## electrical characteristics, $V_{CC}$ = 5 V, $T_C$ = 25°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
V <sub>(BR)</sub> DSX	Drain-source breakdown voltage	I <sub>D</sub> = 1 mA			45			V
V <sub>SD</sub>	Source-drain diode forward voltage	I <sub>F</sub> = 250 mA,	See Note 3			0.85	1	V
Iн	High-level input current	V <sub>CC</sub> = 5.5 V,	$V_I = V_{CC}$				1	μΑ
۱ <sub>IL</sub>	Low-level input current	V <sub>CC</sub> = 5.5 V,	$V_{I} = 0$				-1	μΑ
ICC	Logic supply current	I <sub>O</sub> = 0,	All inputs low			15	100	μΑ
I <sub>N</sub>	Nominal current	V <sub>DS(on)</sub> = 0.5 V See Notes 5, 6,	′,  I <sub>N</sub> = I <sub>D</sub> , and 7	T <sub>C</sub> = 85°C,		250		mA
Inev	Off-state drain current	V <sub>DS</sub> = 40 V				0.05	1	
IDSX	On-state drain current	V <sub>DS</sub> = 40 V,	T <sub>C</sub> = 125°C			0.15	5	μA
		I <sub>D</sub> = 250 mA,	$V_{CC} = 4.5 V$			1.3	2	
<sup>r</sup> DS(on)	Static drain-source on-state resistance	I <sub>D</sub> = 250 mA, V <sub>CC</sub> = 4.5 V	T <sub>C</sub> = 125°C,	See Notes 5 and 6 and Figures 8 and 9		2	3.2	Ω
		I <sub>D</sub> = 500 mA,	V <sub>CC</sub> = 4.5 V			1.3	2	

## switching characteristics, V<sub>CC</sub> = 5 V, T<sub>C</sub> = 25°C

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<sup>t</sup> PLH	Propagation delay time, low-to-high-level output from D			625		ns
<sup>t</sup> PHL	Propagation delay time, high-to-low-level output from D	C <sub>L</sub> = 30 pF, I <sub>D</sub> = 250 mA,		140		ns
tr	Rise time, drain output	See Figures 1, 2, and $10$		650		ns
t <sub>f</sub>	Fall time, drain output			400		ns
ta	Reverse-recovery-current rise time	I <sub>F</sub> = 250 mA, di/dt = 20 A/µs,		100		
t <sub>rr</sub>	Reverse-recovery time	See Notes 5 and 6 and Figure 3		300		ns

NOTES: 3. Pulse duration  $\leq 100 \ \mu$ s, duty cycle  $\leq 2\%$ 

5. Technique should limit  $T_J-T_C$  to 10°C maximum.

6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

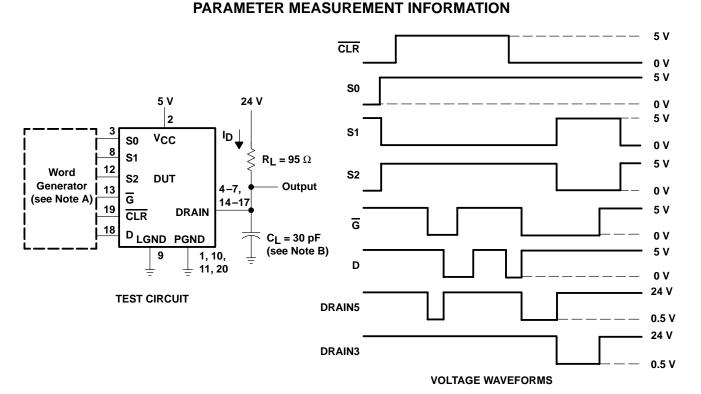
Nominal current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at T<sub>C</sub> = 85°C.

#### thermal resistance

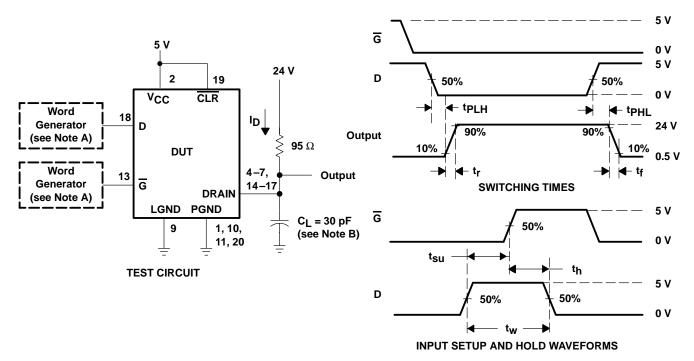
PARAMETER			TEST CONDITIONS	MIN	MAX	UNIT
D		DW package	All Q outputs with agual power		111	°C AN
R <sub>0JA</sub> Thermal resistance	Thermal resistance junction-to-ambient	N package	All 8 outputs with equal power		108	°C/W



SLIS009A - APRIL 1992 - REVISED SEPTEMBER 1995





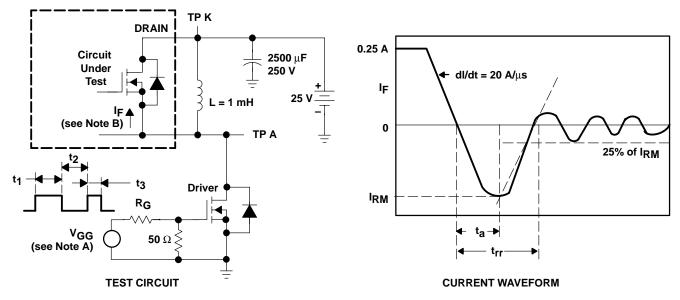




- NOTES: A. The word generator has the following characteristics:  $t_f \le 10$  ns,  $t_f \le 10$  ns,  $t_W = 300$  ns, pulsed repetition rate (PRR) = 5 kHz,  $Z_O = 50 \ \Omega$ .
  - B. C<sub>L</sub> includes probe and jig capacitance.



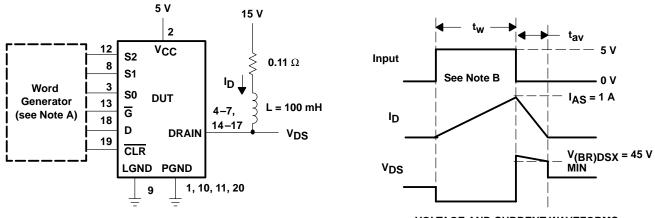
SLIS009A – APRIL 1992 – REVISED SEPTEMBER 1995



#### PARAMETER MEASUREMENT INFORMATION

- NOTES: A. The V<sub>GG</sub> amplitude and R<sub>G</sub> are adjusted for di/dt = 20 A/ $\mu$ s. A V<sub>GG</sub> double-pulse train is used to set I<sub>F</sub> = 0.25 A, where t<sub>1</sub> = 10  $\mu$ s, t<sub>2</sub> = 7  $\mu$ s, and t<sub>3</sub> = 3  $\mu$ s.
  - B. The DRAIN terminal under test is connected to the TP K test point. All other terminals are connected together and connected to the TP A test point.

#### Figure 3. Reverse-Recovery-Current Test Circuit and Waveforms of Source-Drain Diode





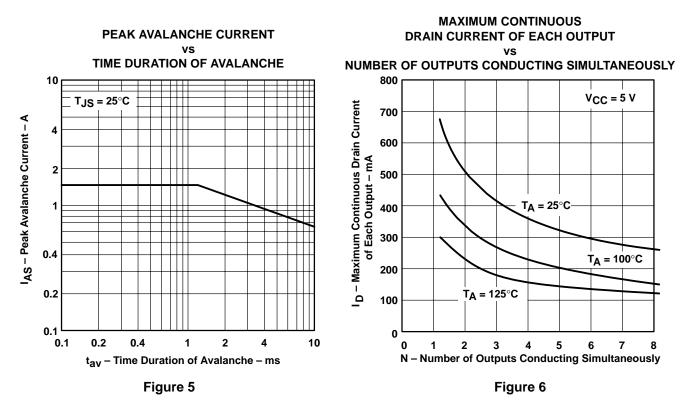


- NOTES: A. The pulse generator has the following characteristics:  $t_f \le 10$  ns,  $t_f \le 10$  ns,  $Z_0 = 50 \Omega$ .
  - B. Input pulse duration, t<sub>W</sub>, is increased until peak current I<sub>AS</sub> = 1 A. Energy test level is defined as  $E_{AS} = I_{AS} \times V_{(BR)DSX} \times t_{aV}/2 = 75$  mJ.

Figure 4. Single-Pulse Avalanche Energy Test Circuit and Waveforms

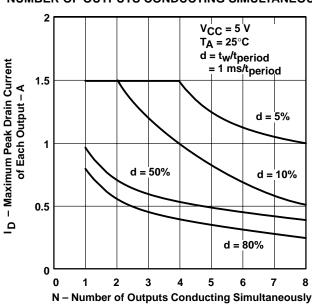


SLIS009A - APRIL 1992 - REVISED SEPTEMBER 1995



**TYPICAL CHARACTERISTICS** 

MAXIMUM PEAK DRAIN CURRENT OF EACH OUTPUT vs

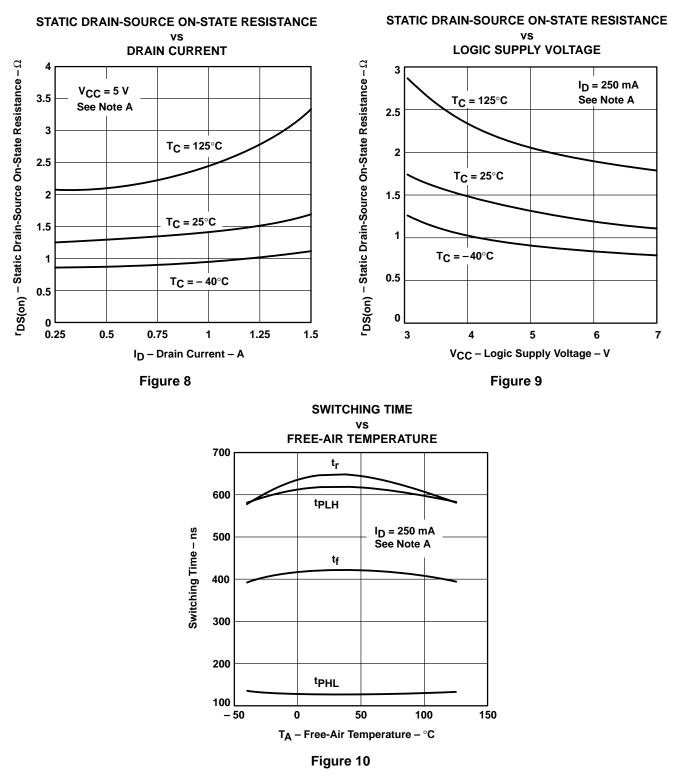


NUMBER OF OUTPUTS CONDUCTING SIMULTANEOUSLY

Figure 7



SLIS009A - APRIL 1992 - REVISED SEPTEMBER 1995



#### **TYPICAL CHARACTERISTICS**

NOTE A: Technique should limit  $T_J-T_C$  to 10°C maximum.



### PACKAGING INFORMATION

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
TPIC6259DW	ACTIVE	SOIC	DW	20	25	TBD	CU NIPDAU	Level-1-220C-UNLIM
TPIC6259DWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPIC6259DWR	ACTIVE	SOIC	DW	20	2000	TBD	CU NIPDAU	Level-1-220C-UNLIM
TPIC6259DWRG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPIC6259N	ACTIVE	PDIP	Ν	20	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

**Important Information and Disclaimer:**The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

DW (R-PDSO-G20)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).

D. Falls within JEDEC MS-013 variation AC.



# N (R-PDIP-T\*\*)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- $\triangle$  The 20 pin end lead shoulder width is a vendor option, either half or full width.



#### **IMPORTANT NOTICE**

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

TI products are not authorized for use in safety-critical applications (such as life support) where a failure of the TI product would reasonably be expected to cause severe personal injury or death, unless officers of the parties have executed an agreement specifically governing such use. Buyers represent that they have all necessary expertise in the safety and regulatory ramifications of their applications, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of TI products in such safety-critical applications, notwithstanding any applications-related information or support that may be provided by TI. Further, Buyers must fully indemnify TI and its representatives against any damages arising out of the use of TI products in such safety-critical applications.

TI products are neither designed nor intended for use in military/aerospace applications or environments unless the TI products are specifically designated by TI as military-grade or "enhanced plastic." Only products designated by TI as military-grade meet military specifications. Buyers acknowledge and agree that any such use of TI products which TI has not designated as military-grade is solely at the Buyer's risk, and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI products are neither designed nor intended for use in automotive applications or environments unless the specific TI products are designated by TI as compliant with ISO/TS 16949 requirements. Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, TI will not be responsible for any failure to meet such requirements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

Products		Applications	
Amplifiers	amplifier.ti.com	Audio	www.ti.com/audio
Data Converters	dataconverter.ti.com	Automotive	www.ti.com/automotive
DSP	dsp.ti.com	Broadband	www.ti.com/broadband
Clocks and Timers	www.ti.com/clocks	Digital Control	www.ti.com/digitalcontrol
Interface	interface.ti.com	Medical	www.ti.com/medical
Logic	logic.ti.com	Military	www.ti.com/military
Power Mgmt	power.ti.com	Optical Networking	www.ti.com/opticalnetwork
Microcontrollers	microcontroller.ti.com	Security	www.ti.com/security
RFID	www.ti-rfid.com	Telephony	www.ti.com/telephony
RF/IF and ZigBee® Solutions	www.ti.com/lprf	Video & Imaging	www.ti.com/video
		Wireless	www.ti.com/wireless

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2008, Texas Instruments Incorporated